

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|-------|--|---|------------------|---------|------------------|
| L1 | 13146 | ((438/149) or (438/151) or (438/164) or (438/166) or (438/311) or (438/412) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/489) or (438/490) or (438/595) or (438/596) or (438/704) or (438/706) or (438/735) or (438/745) or (438/764) or (438/795) or (438/800) or (438/902)).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/01/30 16:01 |
| L2 | 8 | 1 and ((silicon near2 spacer\$1) near5 ((active adj(region\$1 or layer\$1)) or channel\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/30 16:01 |
| S1 | 10057 | ((438/149) or (438/151) or (438/164) or (438/166) or (438/311) or (438/412) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/489) or (438/490) or (438/595) or (438/596) or (438/704) or (438/406) or (438/735) or (438/745) or (438/764) or (438/795) or (438/800) or (438/902)).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/01/30 16:01 |
| S2 | 12 | ("4330363") or ("4592799") or ("5021119") or ("5395481") or ("6495405")).PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2004/12/08 23:06 |
| S3 | 2901 | ((polycrystalline near2 silicon) or (poly adj silicon)) near2 (tft or ((thin near2 film) near2 transistor\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 17:34 |
| S4 | 1053 | ((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or (sidewall near2 spacer\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 21:19 |

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| S5 | 8 | S3 and S4 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 17:36 |
| S6 | 1 | S1 and S5 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 17:36 |
| S7 | 1152 | ((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or capp\$3 or (capp\$3 near2 (layer or film)) or (sidewall near2 spacer\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 18:04 |
| S8 | 4082 | S7 and3 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 17:39 |
| S9 | 12 | S7 and S3 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 17:39 |
| S10 | 1 | S9 and S1 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 17:39 |
| S11 | 11 | S9 not S10 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 17:40 |
| S12 | 16 | ((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or (sidewall near2 spacer\$1)) same (active near2 (layer\$1 or film\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 17:44 |

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| S13 | 16 | ((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or capp\$3 or (capp\$3 near2 (layer or film)) or (sidewall near2 spacer\$1)) same (active near2 (layer\$1 or film\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 17:54 |
| S14 | 6 | ((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or capp\$3 or (capp\$3 near2 (layer or film)) or (sidewall near2 spacer\$1)) near10 (active near2 (layer\$1 or film\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 17:52 |
| S15 | 10 | S13 not S14 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 17:52 |
| S16 | 0 | ("2004/0026738").URPN | USPAT | OR | OFF | 2004/12/08 17:53 |
| S17 | 123 | ((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or capp\$3 or (capp\$3 near2 (layer or film)) or (sidewall near2 spacer\$1))and (active near2 (layer\$1 or film\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 17:55 |
| S18 | 107 | S17 not S13 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 17:55 |
| S19 | 33 | ((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or capp\$3 or (capp\$3 near2 (layer or film)) or (sidewall near2 spacer\$1)) same (crystall\$7 or recrystall\$7) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 18:05 |
| S20 | 7 | S19 and (active near2 (layer\$1 or film\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 18:07 |
| S21 | 0 | S19 not S7 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 18:08 |

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| S22 | 26 | S19 not S20 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 18:09 |
| S23 | 106 | ((LTPS adj TFT) or (low adj temperature adj polycrystalline adj silicon adj thin adj film adj transistor)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 21:21 |
| S24 | 10057 | ((438/149) or (438/151) or (438/164) or (438/166) or (438/311) or (438/412) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/489) or (438/490) or (438/595) or (438/596) or (438/704) or (438/406) or (438/735) or (438/745) or (438/764) or (438/795) or (438/800) or (438/902)).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2004/12/08 21:21 |
| S25 | 103 | S23 and "1" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 21:26 |
| S26 | 21 | S23 and S24 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 21:22 |
| S27 | 75 | S23 and (amorphous) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 22:30 |
| S28 | 19 | S27 and S24 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 21:26 |

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|-----|-------|--|---|----|-----|------------------|
| S29 | 42860 | (spc or (solid adj phas adj crystallization)) or (milc or (metal adj induced adj lateral adj crystallization)) or (ela or (excimer adj laser adj annealing)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 22:33 |
| S30 | 27 | S29 and S23 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 22:33 |
| S31 | 0 | ("2004/0217424").URPN. | USPAT | OR | OFF | 2004/12/08 22:38 |
| S32 | 1 | ("6242292").PN. | USPAT | OR | OFF | 2004/12/08 22:38 |
| S33 | 52 | ("3848104" "4046618" "4059461" "4083272" "4160263" "4234358" "4249960" "4266986" "4309225" "4328553" "4341569" "4370175" "4439245" "4463028" "4468551" "4469551" "4545823" "4734550" "4764485" "4803528" "4835704" "4862227" "4937618" "4942058" "4956539" "4970366" "5217921" "5219786" "5221365" "5247375" "5313076" "5352291" "5365875" "5372836" "5413958" "5424230" "5424244" "5432122" "5477073" "5561081" "5572046" "5578520" "5589406" "5612251" "5622814" "5648277" "5696003" "5708252" "5712191" "5736414" "5756364" "5858473").PN. | US-PGPUB; USPAT; USOCR | OR | OFF | 2004/12/08 22:40 |
| S34 | 20 | ((("5365080") or ("5847419") or ("6607948") or ("6674100") or ("5063166") or ("4962051") or ("4962051") or ("4914053") or ("4868614"))).PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2004/12/08 23:10 |
| S35 | 2 | ("5818053").PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2004/12/08 23:10 |

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| S36 | 10741 | ((438/149) or (438/151) or (438/164) or (438/166) or (438/311) or (438/412) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/489) or (438/490) or (438/595) or (438/596) or (438/704) or (438/406) or (438/735) or (438/745) or (438/764) or (438/795) or (438/800) or (438/902)).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/05/13 15:38 |
| S37 | 121 | S36 and ((polysilicon near spacer\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/13 16:13 |
| S38 | 0 | S36 and ((polysilicon near spacer\$1) near (active adj (layer\$1 or film\$1))) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/13 15:53 |
| S39 | 1 | S36 and ((polysilicon near spacer\$1) same (active adj (layer\$1 or film\$1))) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/13 15:57 |
| S40 | 0 | ((polysilicon near spacer\$1) near (active adj (layer\$1 or film\$1))) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/13 15:53 |
| S41 | 4 | ((polysilicon near spacer\$1) same (active adj (layer\$1 or film\$1))) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/13 15:55 |
| S42 | 16 | ((polysilicon near spacer\$1) and (active adj (layer\$1 or film\$1))) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/13 15:55 |

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| S43 | 0 | S36 and ((polysilicon near sidewall near spacer\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/13 15:57 |
| S44 | 33 | S36 and ((polysilicon near sidewall near spacer\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/13 16:04 |
| S45 | 1 | S44 and (active adj (layer\$1 or film\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/13 15:58 |
| S46 | 10473 | (polysilicon near\$3 spacer\$1) same (active near2 (layer\$1 or film\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/13 16:06 |
| S47 | 2040 | (polysilicon near\$3 spacer\$1) near (active near2 (layer\$1 or film\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/13 16:06 |
| S48 | 0 | (polysilicon near spacer\$1) near (active near2 (layer\$1 or film\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/13 16:06 |
| S49 | 34 | (polysilicon near spacer\$1) same (active near2 (layer\$1 or film\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/13 16:10 |
| S50 | 153 | (polysilicon near spacer\$1) and (active near2 (layer\$1 or film\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/13 16:10 |
| S51 | 1 | ("5589406").PN. | USPAT | OR | OFF | 2005/05/13 16:31 |

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| S52 | 395 | ((ltps adj tft) or ((low near temperature) near transistor\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/13 16:34 |
| S53 | 3 | S52 and (polysilicon near2 spacer\$1) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/13 16:36 |
| S54 | 46 | S52 and (active near (layer\$1 or film\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/13 16:41 |
| S55 | 5 | S54 and spacer\$1 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/13 16:38 |
| S56 | 5 | S54 and ((spacer\$1 or sidewall) same (active near (layer\$1 or film\$1))) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/13 16:39 |
| S57 | 1 | (soi near mosfet) same (polysilicon near spacer\$1) same (active near2 (layer\$1 or film\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/13 16:42 |
| S58 | 4 | (soi near mosfet) same (spacer\$1 same (active near2 (layer\$1 or film\$1))) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/13 16:44 |
| S59 | 64 | (soi near mosfet) same: spacer\$1 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/13 16:44 |
| S60 | 36 | "5589406" | USPAT | OR | OFF | 2005/05/16 17:06 |
| S61 | 1 | ("5589406").PN. | USPAT | OR | OFF | 2005/05/16 17:06 |

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| S62 | 11786 | ((438/149) or (438/151) or (438/164) or (438/166) or (438/311) or (438/412) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/489) or (438/490) or (438/595) or (438/596) or (438/704) or (438/406) or (438/735) or (438/745) or (438/764) or (438/795) or (438/800) or (438/902)).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/01/30 15:44 |
| S63 | 0 | ("1and((siliconnear2spacer\$1)near5((activeadj(region\$1orlayer\$1))orchannel\$1))").PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/01/30 15:45 |
| S64 | 8 | S62 and ((silicon near2 spacer\$1) near5 ((active adj(region\$1 or layer\$1)) or channel\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/30 16:01 |
| S65 | 1318 | (438/151).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/01/30 15:48 |
| S66 | 571 | (438/487).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/01/30 15:49 |
| S67 | 1081 | (438/166).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/01/30 15:49 |
| S68 | 977 | (438/795).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/01/30 15:49 |

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| S69 | 90 | ((silicon near2 spacer\$1) near5 ((active adj(region\$1 or layer\$1)) or channel\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/30 15:51 |
| S70 | 6 | S69 and (crystalliz\$5 or recrystalliz\$5) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/30 15:52 |